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### 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

WWW - For www.nxp.com use www.ween-semi.com

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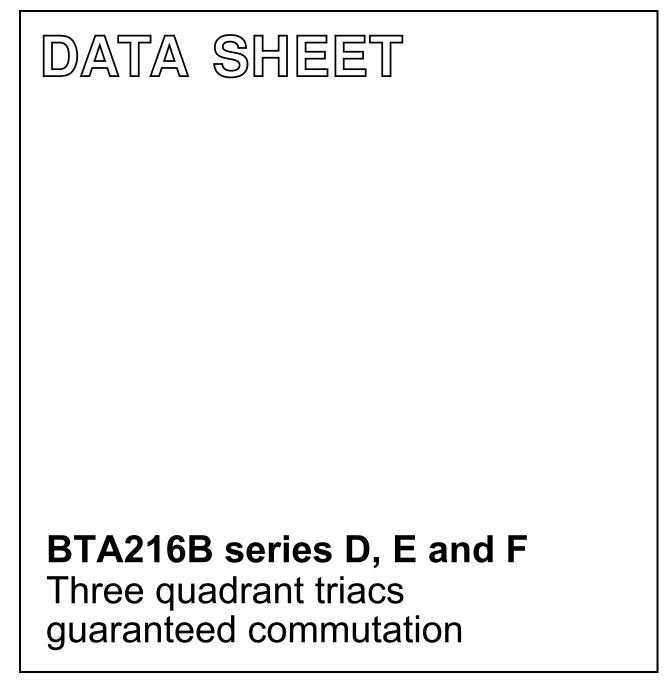
If you have any questions related to this document, please contact our nearest sales office via email or phone (details via <u>salesaddresses@ween-semi.com</u>).

Thank you for your cooperation and understanding,

WeEn Semiconductors



DISCRETE SEMICONDUCTORS



Product specification

April 2002



MAX.

600D

600E

600F

600

16

140

UNIT

٧

А

А

# Three quadrant triacs guaranteed commutation

### BTA216B series D, E and F

### **GENERAL DESCRIPTION**

Passivated guaranteed commutation triacs in a plastic envelope suitable for surface mounting, intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

### **PINNING - SOT404**

## 

QUICK REFERENCE DATA

current

PARAMETER

SYMBOL

 $V_{DRM}$ 

T(RMS)

**PIN CONFIGURATION** 

I<sub>TSM</sub>

### SYMBOL

**BTA216B-**

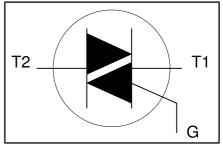
**BTA216B-**

**BTA216B-**

Repetitive peak off-state

Non-repetitive peak on-state

voltages RMS on-state current



# PINDESCRIPTION1main terminal 12main terminal 23gatembmain terminal 2

### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL                                  | PARAMETER   | CONDITIONS   | MIN. | MAX.             | UNIT        |
|---|---|--|------|------------------|-------------|
| V <sub>DRM</sub>                        | Repetitive peak off-state   |  | -    | 600 <sup>1</sup> | V           |
|   | voltages<br>RMS on-state current  | full sine wave;  |      | 16               | А           |
| I <sub>T(RMS)</sub><br>I <sub>TSM</sub> | Non-repetitive peak   | $T_{mb} \le 99 \degree C$<br>full sine wave;<br>$T_i = 25 \degree C$ prior to                        | -    | 10               | A           |
|   |   | surge<br>t = 20 ms<br>t = 16.7 ms  | -    | 140<br>150       | A<br>A      |
| l²t<br>dl <sub>⊤</sub> /dt              | I <sup>2</sup> t for fusing<br>Repetitive rate of rise of<br>on-state current after | t = 10  ms<br>$I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$<br>$dI_G/dt = 0.2 \text{ A}/\mu\text{s}$ | -    | 98<br>100        | A²s<br>A/μs |
| I <sub>GM</sub><br>P <sub>GM</sub>      | triggering<br>Peak gate current<br>Peak gate power                                  | over any 20 ms   | -    | 2<br>5<br>0.5    | A<br>W<br>W |
| P <sub>G(AV)</sub><br>T <sub>stq</sub>  | Average gate power<br>Storage temperature   | period   | -40  | 150              | °C<br>O     |
| T <sub>stg</sub><br>T <sub>j</sub>      | Operating junction<br>temperature   |  | -    | 125              | °C          |

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

# Three quadrant triacs guaranteed commutation

### BTA216B series D, E and F

### THERMAL RESISTANCES

| SYMBOL                                      | PARAMETER | CONDITIONS   | MIN.   | TYP.         | MAX.            | UNIT              |
|---|-----------|--|--------|--------------|-----------------|-------------------|
| R <sub>th j-mb</sub><br>R <sub>th j-a</sub> |           | full cycle<br>half cycle<br>minimum footprint, FR4 board | -<br>- | -<br>-<br>55 | 1.2<br>1.7<br>- | K/W<br>K/W<br>K/W |

### STATIC CHARACTERISTICS

 $T_j = 25$  °C unless otherwise stated

| SYMBOL                            | PARAMETER                                | CONDITIONS   | MIN.           | MAX.           |                 | UNIT           |                |
|-----------------------------------|--|--|----------------|----------------|-----------------|----------------|----------------|
|                                   |  | BTA216B-   |                | D              | E               | F              |                |
| I <sub>GT</sub>                   | Gate trigger current <sup>2</sup>        | $V_{D} = 12 V; I_{T} = 0.1 A$<br>T2+ G+<br>T2+ G-<br>T2- G-      | -<br>-<br>-    | 5<br>5<br>5    | 10<br>10<br>10  | 25<br>25<br>25 | mA<br>mA<br>mA |
| IL.                               | Latching current                         | $V_{D} = 12 V; I_{GT} = 0.1 A$<br>T2+G+<br>T2+G-<br>T2-G-        | -<br>-<br>-    | 15<br>25<br>25 | 25<br>30<br>30  | 30<br>40<br>40 | mA<br>mA<br>mA |
| I <sub>H</sub>                    | Holding current                          | $V_{\rm D} = 12 \text{ V}; \text{ I}_{\rm GT} = 0.1 \text{ A}$   | -              | 15             | 25              | 30             | mA             |
|                                   |  |  | D, E, F        |                |                 |                |                |
| V <sub>T</sub><br>V <sub>GT</sub> | On-state voltage<br>Gate trigger voltage |  | -<br>-<br>0.25 |                | 1.5<br>1.5<br>- |                | V<br>V<br>V    |
| I <sub>D</sub>                    | Off-state leakage current                | $V_{\rm D} = V_{\rm DRM(max)}; T_{\rm j} = 125 ^{\circ} {\rm C}$ | -              |                | 0.5             |                | mA             |

### **DYNAMIC CHARACTERISTICS**

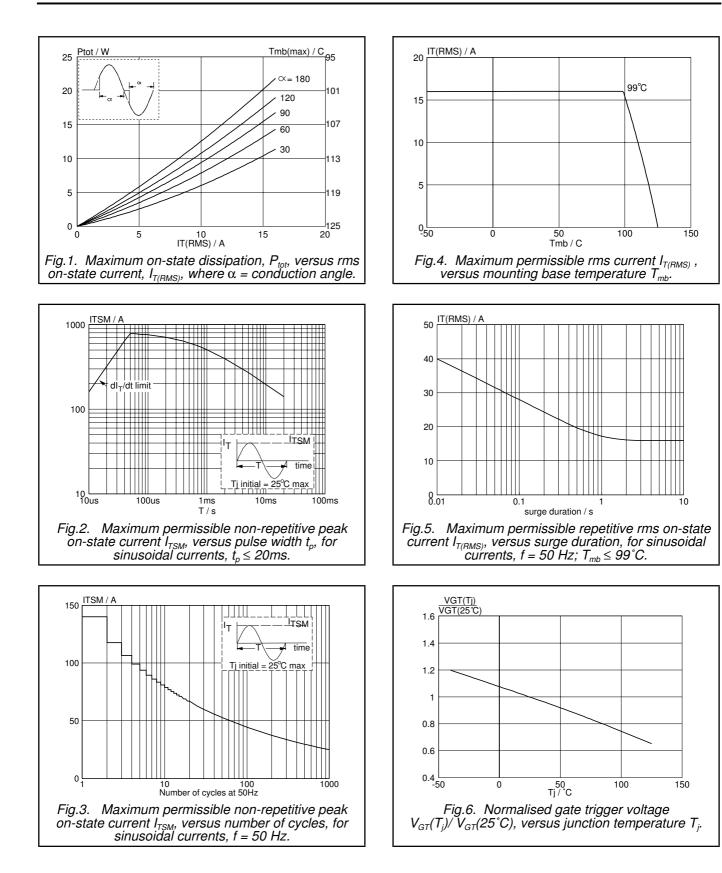
 $T_i = 25$  °C unless otherwise stated

| SYMBOL                | PARAMETER   | CONDITIONS  |     | MIN. |    | MAX. | UNIT |
|-----------------------|---|---|-----|------|----|------|------|
|                       |   | BTA216B-  | D   | E    | F  |      |      |
| dV <sub>D</sub> /dt   | Critical rate of rise of off-state voltage        | $V_{DM} = 67\% V_{DRM(max)};$<br>$T_j = 110$ °C; exponential  | 30  | 60   | 70 | -    | V/µs |
| dl <sub>com</sub> /dt | Critical rate of change of<br>commutating current | waveform; gate open circuit<br>$V_{DM} = 400 \text{ V}; \text{ T}_{j} = 125 \text{ °C};$<br>$I_{T(RMS)} = 16 \text{ A};$<br>$dV_{com}/dt = 10V/\mu s; gate$<br>open circuit | 2.5 | 6.2  | 18 | -    | A/ms |
| dl <sub>com</sub> /dt | Critical rate of change of<br>commutating current | $V_{DM} = 400 \text{ V}; \text{ T}_{j} = 125 \text{ °C};$<br>$I_{T(RMS)} = 16 \text{ A};$<br>$dV_{com}/dt = 0.1 \text{ V}/\mu\text{s}; \text{ gate}$<br>open circuit        | 12  | 20   | 50 | -    | A/ms |

<sup>2</sup> Device does not trigger in the T2-, G+ quadrant.

# Three quadrant triacs guaranteed commutation

### BTA216B series D, E and F



BTA216B series D, E and F

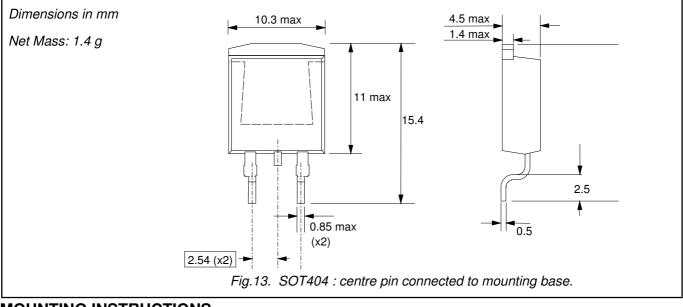
# Three quadrant triacs guaranteed commutation

#### IT / A IGT(Tj) IGT(25℃) 50 Tj = 125 C Tj = 25 C 3 — T2+ G+ — T2+ Gtyp ma - T2- G-40 2.5 Vo = 1.195 V Rs = 0.018 Ohms 2 30 1.5 20 1 10 0.5 0 L 0 0 1.5 VT / V 150 0.5 2 2.5 3 -50 0 тј/℃ 100 1 Fig.7. Normalised gate trigger current $I_{GT}(T_j)/I_{GT}(25^{\circ}C)$ , versus junction temperature $T_{j}$ . Fig.10. Typical and maximum on-state characteristic. 10 \_\_\_\_\_(K/W) IL(Tj) IL(25°C) 3 25 1 bidirectional 2 0.1 1.5 1 0.01 0.5 0.001 – 10us 0 -50 0.1ms 10ms 0.1s 1s 10s 50 Tj /℃ 100 1ms 0 150 tp/s Fig.11. Transient thermal impedance $Z_{th j-mb}$ , versus Fig.8. Normalised latching current $I_L(T_i)/I_L(25^{\circ}C)$ , versus junction temperature $T_{i}$ pulse width $t_{p}$ dlcom/dt (A/ms) IH(Tj) 100 3 IH(25°C F TYPE E TYPE D TYPE 2.5 2 10 1.5 1 0.5 1 0 -50 50 Tj /℃ 20 40 60 100 120 140 100 150 80 Tj/°C 0 Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$ , versus junction temperature $T_j$ . Fig.12. Mimimum, critical rate of change of commutating current $dI_{com}/dt$ versus junction temperature, $dV_{com}/dt = 10V/\mu s$ .

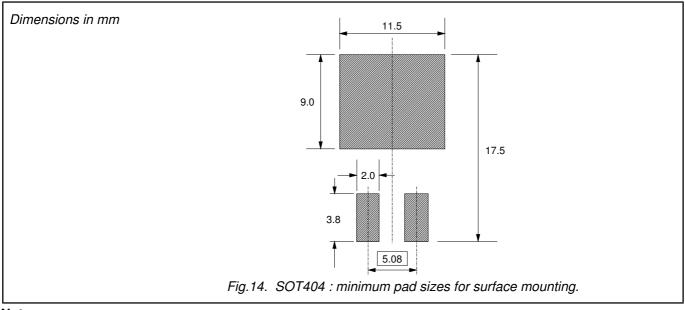
# Three quadrant triacs guaranteed commutation

### BTA216B series D, E and F

### **MECHANICAL DATA**



### **MOUNTING INSTRUCTIONS**



### Notes

1. Plastic meets UL94 V0 at 1/8".

### Legal information

#### DATA SHEET STATUS

| DOCUMENT<br>STATUS <sup>(1)</sup> PRODUCT<br>STATUS <sup>(2)</sup> |               | DEFINITION  |  |  |  |
|--|---------------|---|--|--|--|
| Objective data sheet   | Development   | This document contains data from the objective specification for product development. |  |  |  |
| Preliminary data sheet   | Qualification | This document contains data from the preliminary specification.                       |  |  |  |
| Product data sheet   | Production    | This document contains the product specification.                                     |  |  |  |

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